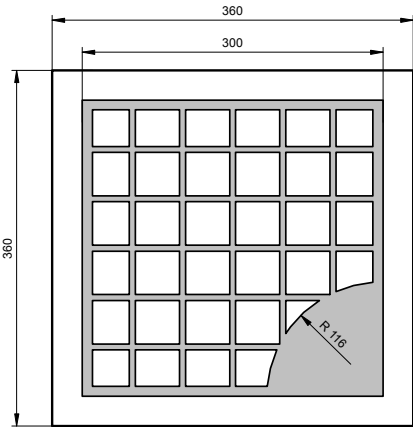


Radiation	Type	Technology	Electrodes
Infrared	MQW	InGaAs/InP	P (anode) up

 <p style="text-align: center;">LED-11</p>	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 μm <u>anode</u> gold alloy, 1.5 μm <u>cathode</u> gold alloy, 0.5 μm	

### Maximum Ratings

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I <sub>F</sub>			100	mA
Peak forward current	t <sub>p</sub> ≤ 50 μs, t <sub>p</sub> /T = 1/2	I <sub>FM</sub>			200	mA

### Optical and Electrical Characteristics

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 20 mA	V <sub>F</sub>		0.75	0.9	V
Forward voltage	I <sub>F</sub> = 100 mA	V <sub>F</sub>		0.85	1.0	V
Reverse voltage	I <sub>R</sub> = 100 μA	V <sub>R</sub>	5			V
Radiant power <sup>1</sup>	I <sub>F</sub> = 20 mA	Φ <sub>e</sub>	0.47	0.7		mW
Radiant power <sup>1</sup>	I <sub>F</sub> = 100 mA	Φ <sub>e</sub>	1.7	2.5		mW
Radiant power <sup>2</sup>	I <sub>F</sub> = 100 mA	Φ <sub>e</sub>		5.0		mW
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>	1530	1550	1570	nm
Spectral bandwidth at 50%	I <sub>F</sub> = 100 mA	Δλ <sub>0.5</sub>		130		nm
Switching time	I <sub>F</sub> = 100 mA	t <sub>r</sub> , t <sub>f</sub>		10		ns

<sup>1</sup>Measured on bare chip on TO-18 header with *EPIGAP* equipment

<sup>2</sup>Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

### Labeling

Type	Lot N°	Φ <sub>e</sub> (typ) [mW]	V <sub>F</sub> (typ) [V]	Quantity
ELC-1550-17				

**Packing:** Chips on adhesive film with wire-bond side on top